











CC1120 SWRS112H – JUNE 2011 – REVISED JULY 2015

# CC1120 High-Performance RF Transceiver for Narrowband Systems

#### 1 Device Overview

#### 1.1 Features

- High-Performance, Single-Chip Transceiver
  - Adjacent Channel Selectivity:
     64 dB at 12.5-kHz Offset
  - Blocking Performance: 91 dB at 10 MHz
  - Excellent Receiver Sensitivity:
    - -123 dBm at 1.2 kbps
    - –110 dBm at 50 kbps
    - -127 dBm Using Built-in Coding Gain
  - Very Low Phase Noise:
    - -111 dBc/Hz at 10-kHz Offset
- Suitable for Systems Targeting ETSI Category 1 Compliance in 169-MHz and 433-MHz Bands
- High Spectral Efficiency (9.6 kbps in 12.5-kHz Channel in Compliance With FCC Narrowbanding Mandate)
- · Separate 128-Byte RX and TX FIFOs
- Support for Seamless Integration With the CC1190 Device for Increased Range Giving up to 3-dB Improvement in Sensitivity and up to +27-dBm Output Power
- Power Supply
  - Wide Supply Voltage Range (2.0 V to 3.6 V)
  - Low Current Consumption:
    - RX: 2 mA in RX Sniff Mode
    - RX: 17 mA Peak Current in Low-Power Mode
    - RX: 22 mA Peak Current in High-Performance Mode
    - TX: 45 mA at +14 dBm
  - Power Down: 0.12 μA (0.5 μA With eWOR Timer Running)
- Programmable Output Power up to +16 dBm With 0.4-dB Step Size

#### 1.2 Applications

- Narrowband Ultra-Low-Power Wireless Systems With Channel Spacing Down to 12.5 kHz
- 169-, 315-, 433-, 868-, 915-, 920-, 950-MHz ISM/SRD Band
- Wireless Metering and Wireless Smart Grid (AMR and AMI)

- · Automatic Output Power Ramping
- Configurable Data Rates: 0 to 200 kbps
- Supported Modulation Formats: 2-FSK, 2-GFSK, 4-FSK, 4-GFSK, MSK, OOK
- WaveMatch: Advanced Digital Signal Processing for Improved Sync Detect Performance
- RoHS-Compliant 5-mm x 5-mm No-Lead QFN 32-Pin Package (RHB)
- Regulations Suitable for Systems Targeting Compliance With
  - Europe: ETSI EN 300 220, ETSI EN 54-25
  - US: FCC CFR47 Part 15, FCC CFR47 Part 90, 24, and 101
  - Japan: ARIB RCR STD-T30, ARIB STD-T67, ARIB STD-T108
- · Peripherals and Support Functions
  - Enhanced Wake-On-Radio (eWOR)
     Functionality for Automatic Low-Power Receive
     Polling
  - Includes Functions for Antenna Diversity Support
  - Support for Retransmissions
  - Support for Automatic Acknowledge of Received Packets
  - TCXO Support and Control, Also in Power Modes
  - Automatic Clear Channel Assessment (CCA) for Listen-Before-Talk (LBT) Systems
  - Built-in Coding Gain Support for Increased Range and Robustness
  - Digital RSSI Measurement
  - Temperature Sensor
- IEEE 802.15.4g Systems
- Home and Building Automation
- Wireless Alarm and Security Systems
- Industrial Monitoring and Control
- Wireless Healthcare Applications
- Wireless Sensor Networks and Active RFID
- Private Mobile Radios

### 1.3 Description

The CC1120 device is a fully integrated single-chip radio transceiver designed for high performance at very low-power and low-voltage operation in cost-effective wireless systems. All filters are integrated, thus removing the need for costly external SAW and IF filters. The device is mainly intended for Industrial, Scientific, and Medical (ISM) applications and Short Range Device (SRD) frequency bands at 164 to 192 MHz, 274 to 320 MHz, 410 to 480 MHz, and 820 to 960 MHz.

The CC1120 device provides extensive hardware support for packet handling, data buffering, burst transmissions, clear channel assessment, link quality indication, and wake-on-radio. The main operating parameters of the CC1120 device can be controlled through an SPI interface. In a typical system, the CC1120 device is used with a microcontroller and only a few external passive components.

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
CC1120	VQFN (32)	5.00 mm × 5.00 mm

(1) For more information, see Section 8, Mechanical Packaging and Orderable Information

#### 1.4 Functional Block Diagram

Figure 1-1 shows the system block diagram of the CC1120 device.

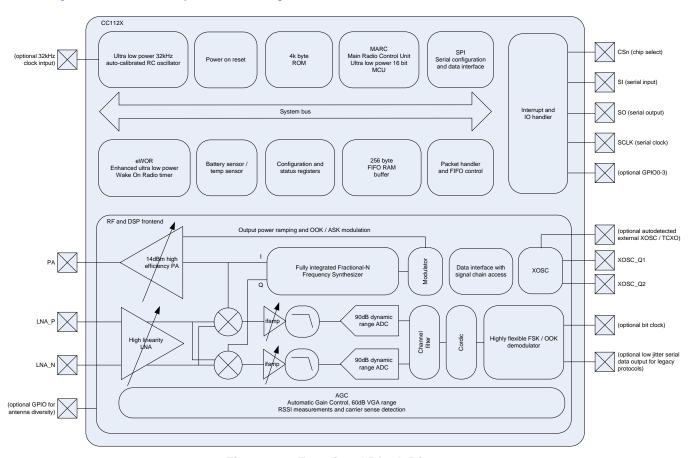


Figure 1-1. Functional Block Diagram



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### 2 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Chan	ges from Revision G (September 2014) to Revision H	Page
•	Moved storage temperature range back to Absolute Maximum Ratings table	<u>7</u> <u>14</u> <u>14</u> ə. <u>14</u>
Chan	ges from Revision F (July 2014) to Revision G	Page
•	Added "Ambient" to the temperature range condition and removed Tj from Temperature range	



### 3 Terminal Configuration and Functions

### 3.1 Pin Diagram

Figure 3-1 shows pin names and locations for the CC1120 device.

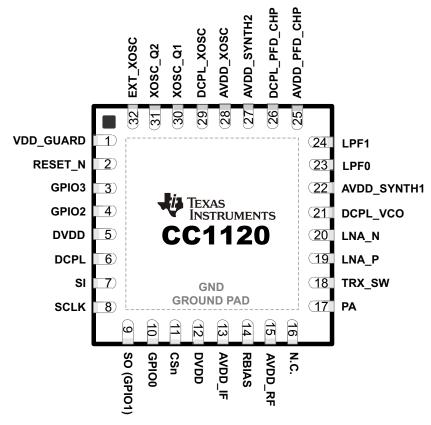


Figure 3-1. Package 5-mm × 5-mm QFN

## 3.2 Pin Configuration

The following table lists the pinout configuration for the CC1120 device.

	PIN		THO THE COTTED device.
NO.	NAME	TYPE	DESCRIPTION
1	VDD_GUARD	Power	2.0–3.6 V VDD
2	RESET_N	Digital input	Asynchronous, active-low digital reset
3	GPIO3	Digital I/O	General-purpose I/O
4	GPIO2	Digital I/O	General-purpose I/O
5	DVDD	Power	2.0–3.6 VDD to internal digital regulator
6	DCPL	Power	Digital regulator output to external decoupling capacitor
7	SI	Digital input	Serial data in
8	SCLK	Digital input	Serial data clock
9	SO(GPIO1)	Digital I/O	Serial data out (general-purpose I/O)
10	GPIO0	Digital I/O	General-purpose I/O
11	CSn	Digital input	Active-low chip select
12	DVDD	Power	2.0–3.6 V VDD
13	AVDD_IF	Power	2.0–3.6 V VDD
14	RBIAS	Analog	External high-precision resistor
15	AVDD_RF	Power	2.0–3.6 V VDD
16	N.C.	_	Not connected
17	PA	Analog	Single-ended TX output (requires DC path to VDD)
18	TRX_SW	Analog	TX and RX switch. Connected internally to GND in TX and floating (high-impedance) in RX.
19	LNA_P	Analog	Differential RX input (requires DC path to ground)
20	LNA_N	Analog	Differential RX input (requires DC path to ground)
21	DCPL_VCO	Power	Pin for external decoupling of VCO supply regulator
22	AVDD_SYNTH1	Power	2.0–3.6 V VDD
23	LPF0	Analog	External loop filter components
24	LPF1	Analog	External loop filter components
25	AVDD_PFD_CHP	Power	2.0–3.6 V VDD
26	DCPL_PFD_CHP	Power	Pin for external decoupling of PFD and CHP regulator
27	AVDD_SYNTH2	Power	2.0–3.6 V VDD
28	AVDD_XOSC	Power	2.0–3.6 V VDD
29	DCPL_XOSC	Power	Pin for external decoupling of XOSC supply regulator
30	XOSC_Q1	Analog	Crystal oscillator pin 1 (must be grounded if a TCXO or other external clock connected to EXT_XOSC is used)
31	XOSC_Q2	Analog	Crystal oscillator pin 2 (must be left floating if a TCXO or other external clock connected to EXT_XOSC is used)
32	EXT_XOSC	Digital input	Pin for external clock input (must be grounded if a regular crystal connected to XOSC_Q1 and XOSC_Q2 is used)
_	GND	Ground pad	The ground pad must be connected to a solid ground plane.



#### 4 Specifications

All measurements performed on CC1120EM\_868\_915 rev.1.0.1, CC1120EM\_955 rev.1.2.1, CC1120EM\_420\_470 rev.1.0.1, or CC1120EM\_169 rev.1.2.

#### **Absolute Maximum Ratings**

over operating free-air temperature range (unless otherwise noted)(1)(2)

	,			
		MIN	MAX	UNIT
Supply voltage (VDD, AVDD_x)	All supply pins must have the same voltage	-0.3	3.9	V
Input RF level			+10	dBm
Voltage on any digital pin	Max 3.9 V	-0.3	VDD + 0.3	V
Voltage on analog pins (including DCPL pins)		-0.3	2.0	V
Storage temperature, T <sub>stg</sub>		-40	125	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under general characteristics is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to V<sub>SS</sub> unless otherwise noted.

#### 4.1 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS001 <sup>(1)</sup>	±2	kV
'	V <sub>ESD</sub> discharge (ESD) performance	Charged device model (CDM), per JESD22-C101 <sup>(2)</sup> All pins	±500	٧

JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

#### 4.2 Recommended Operating Conditions (General Characteristics)

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM MAX	UNIT
Voltage supply range	All supply pins must have the same voltage	2.0	3.6	V
Voltage on digital inputs		0	VDD	V
Ambient temperature range		-40	85	°C

#### 4.3 RF Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
		820		960		
		410		480		
Frequency bands	See SWRA398, Using the CC112x/CC1175 at 274 to 320 MHz, for more information	(273.3)		(320)	MHz	
		164		192		
	Contact TI for more information about the use of these frequency bands	(205)		(240)		
		(136.7)		(160)		
	In 820-950 MHz band		30			
Frequency resolution	In 410-480 MHz band		15		Hz	
	In 164–192 MHz band		6			
Data rate	Packet mode	0		200	leboo	
	Transparent mode	0		100	kbps	
Data rate step size			1e-4		bps	

<sup>(2)</sup> JEDEC document JEP157 states that 250-V HBM allows safe manufacturing with a standard ESD control process.



### **Power Consumption Summary**

 $T_{\Lambda} = 25^{\circ}C$ . VDD = 3.0 V if nothing else stated

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
CURRENT CONS	UMPTION: STATIC MODES					
D				134 20 134 50 45 34 50 45 34 54 49 41 32 2 13.4 22 23 15	1	
Power down with r	etention	Low-power RC oscillator running		0.5		μA
XOFF mode		Crystal oscillator / TCXO disabled		170		μΑ
IDLE mode		Clock running, system waiting with no radio activity		1.3		mA
CURRENT CONS	UMPTION, TRANSMIT MODES					
TX current consun	nption +10 dBm	OFO Mile bond (birth morformore mode)		37		mΑ
TX current consun	nption 0 dBm	950-MHz band (nign-performance mode)		26		mA
TX current consun	nption +14 dBm	868-, 915-, and 920-MHz bands (high-		45		mA
TX current consun	nption +10 dBm	performance mode)		34		mA
TX current consun	nption +15 dBm			50		mA
TX current consun	ent consumption 0 dBm  ent consumption +14 dBm ent consumption +10 dBm ent consumption +15 dBm ent consumption +14 dBm ent consumption +14 dBm ent consumption +10 dBm ent consumption +15 dBm ent consumption +15 dBm ent consumption +16 dBm ent consumption +16 dBm ent consumption +16 dBm ent consumption +16 dBm ent consumption +10 dBm ent consumption +10 dBm	434-MHz band (high-performance mode)		45		mA
TX current consun	nption +10 dBm	performance mode)  434-MHz band (high-performance mode)  169-MHz band (high-performance mode)		34		mA
TX current consun	nption +15 dBm			54		mA
TX current consun	mption +15 dBm mption +14 dBm	169-MHz band (high-performance mode)		49		mA
TX current consun	nption +10 dBm			41		mA
LOW-POWER MC	DE <sup>(1)</sup>					
TX current consun	nption +10 dBm			32		mA
CURRENT CONS	UMPTION, RECEIVE MODE (HIG	H-PERFORMANCE MODE)(1)				
	1.2 kbps, 4-byte preamble			2		
RX wait for sync	38.4 kbps, 4-byte preamble	wakes up at regular intervals to look for an incoming packet (2)		13.4		mA
RX peak current	433-, 868-, 915-, 920-, and 950–MHz bands	Peak current consumption during packet		22		mA
•	169-MHz band	reception at the sensitivity threshold		23		
Average current co Check for data pao on Radio	onsumption cket every 1 second using Wake	50 kbps, 5-byte preamble, 40-kHz RC oscillator used as sleep timer	C		μA	
CURRENT CONS	UMPTION, RECEIVE MODE (LOV	V-POWER MODE) <sup>(1)</sup>				
RX peak current Low-power RX mode	1.2 kbps	Peak current consumption during packet reception at the sensitivity level		17		mA

<sup>(1)</sup>  $T_A = 25$ °C, VDD = 3.0 V,  $f_C = 869.5$  MHz if nothing else stated. (2) See the sniff mode design note for more information (SWRA428).



#### 4.5 **Receive Parameters**

All RX measurements made at the antenna connector, to a bit error rate (BER) limit of 1%

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
GENERAL F	RECEIVE PARAMETERS (HIGH-PERFORM)	ANCE MODE) <sup>(1)</sup>		'	
Saturation			+10		dBm
Digital chanr	nel filter programmable bandwidth		8	200	kHz
IIP3, normal	mode	At maximum gain	-14		dBm
IIP3, high lin	earity mode	Using 6-dB gain reduction in front end	-8		dBm
Data rate off	set tolerance	With carrier sense detection enabled and assuming 4-byte preamble	±12%		
	urious ssions 1–13 GHz (VCO leakage at 3.5 GHz) 30 MHz to 1 GHz  868-, 915-, and 920-MHz bands  imum rice 433-MHz band	With carrier sense detection disabled	±0.2%		
Spurious Enurious $1-13 \text{ GHz}$ (VCO leakage at 3.5 GHz)  Radiated emissions measured according ETSI EN 300 220, $f_c = 869.5 \text{ MHz}$ Radiated emissions measured according ETSI EN 300 220, $f_c = 869.5 \text{ MHz}$ Radiated emissions measured according ETSI EN 300 220, $f_c = 869.5 \text{ MHz}$ Radiated emissions measured according ETSI EN 300 220, $f_c = 869.5 \text{ MHz}$	Radiated emissions measured according to	-56		-ID	
emissions	30 MHz to 1 GHz		<-57		dBm
	868-, 915-, and 920-MHz bands		60 + j60 / 30 + j30		
Optimum source impedance	433-MHz band	(Differential or single-ended RX configurations)	100 + j60 / 50 + j30		Ω
	169-MHz band		140 + j40 / 70 + j20		
RX PERFOR	RMANCE IN 950-MHZ BAND (HIGH-PERFO	RMANCE MODE) <sup>(2)</sup>	,		
	•	1.2 kbps, DEV = 4 kHz CHF = 10 kHz <sup>(4)</sup>	-120		
		1.2 kbps, DEV = 20 kHz CHF = 50 kHz <sup>(4)</sup>	-114		
Sensitivity <sup>(3)</sup>		50 kbps 2GFSK, DEV = 25 kHz, CHF = 100 kHz <sup>(4)</sup>	-107		dBm
		200 kbps, DEV = 83 kHz (outer symbols), CHF = 200 kHz <sup>(4)</sup> , 4GFSK <sup>(5)</sup>	-100		
		± 12.5 kHz (adjacent channel)	51		
	1.2 kbps 2FSK, 12.5-kHz channel	± 25 kHz (alternate channel)	52		
	separation, 4-kHz deviation,	± 1 MHz	73		
	10-kHz channel filter	± 2 MHz	76		
		± 10 MHz	81		
		± 50 kHz (adjacent channel)	47		
	1.2 kbps 2ESK 50 kHz shannel	+ 100 kHz (alternate channel)	48		
	1.2 kbps 2FSK, 50-kHz channel separation, 20-kHz deviation,	± 1 MHz	69		
	50-kHz channel filter	± 2 MHz	71		
Blocking		± 10 MHz	78		
and Selectivity		± 200 kHz (adjacent channel)	43		dB
00.00	50 kbps 2GFSK, 200-kHz channel	± 400 kHz (alternate channel)	51		
	separation, 25-kHz deviation, 100-kHz channel filter (Same modulation	± 1 MHz	62		
	format as 802.15.4g Mandatory Mode)	± 2 MHz	65		
	,	± 10 MHz	71		
		± 200 kHz (adjacent channel)	37		
		± 400 kHz (alternate channel)	44		
	200 kbps 4GFSK, 83-kHz deviation (outer	± 1 MHz	55		
	symbols), 200-kHz channel filter, zero IF	± 2 MHz	58		
		± 10 MHz	64		

 <sup>(1)</sup> T<sub>A</sub> = 25°C, VDD = 3.0 V, f<sub>c</sub> = 869.5 MHz if nothing else stated.
 (2) T<sub>A</sub> = 25°C, VDD = 3.0 V if nothing else stated.
 (3) Sensitivity can be improved if the TX and RX matching networks are separated.
 (4) DEV is short for denoting, CHF is short for Channel Filter Bandwidth

BT = 0.5 is used in all GFSK measurements



### **Receive Parameters (continued)**

All RX measurements made at the antenna connector, to a bit error rate (BER) limit of 1%.

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
RX PERFO	RMANCE IN 868-, 915-, AND 920-MHZ BAND	S (HIGH-PERFORMANCE MODE) (2)			
		300 bps with coding gain (using a PN spreading sequence with 4 chips per data bit) DEV = 4 kHz CHF = 10 kHz <sup>(4)</sup>	-127		
		1.2 kbps, DEV = 4 kHz CHF = 10 kHz <sup>(4)</sup>	-123		
		1.2 kbps, DEV = 10 kHz CHF = 42 kHz <sup>(4)</sup>	-120		
ensitivity		1.2 kbps, DEV = 20 kHz CHF = 50 kHz <sup>(4)</sup>	-117		-ID
sensitivity		4.8 kbps OOK	-114		dBm
		38.4 kbps, DEV = 20 kHz CHF = 100 kHz <sup>(4)</sup>	-110		
		50 kbps 2GFSK, DEV = 25 kHz, CHF = 100 kHz $^{(4)}$	-110		
		200 kbps, DEV = 83 kHz (outer symbols), CHF = 200 kHz <sup>(4)</sup> , 4GFSK	-103		
		± 12.5 kHz (adjacent channel)	54		
	1.2-kbps 2-FSK, 12.5-kHz channel	± 25 kHz (alternate channel)	54		
	separation, 4-kHz deviation,	± 1 MHz	75		
	10-kHz channel filter	± 2 MHz	79		
		± 10 MHz	87		
	1.2-kbps 2-FSK, 12.5-kHz channel	± 1 kHz	78		
	separation, using settings optimized for blocking performance (3-kHz deviation, 7.8-kHz channel filter, minimum loop bandwidth)	± 2 kHz	82		
		± 8 MHz	88		
		± 10 MHz	88		
	1.2-kbps 2-FSK, 50-kHz channel	± 50 kHz (adjacent channel)	48		
		+ 100 kHz (alternate channel)	48		
	separation, 20-kHz deviation,	± 1 MHz	69		
	50-kHz channel filter	± 2 MHz	74		
Blocking		± 10 MHz	81		
ınd		+ 100 kHz (adjacent channel)	42		dB
Selectivity	38.4-kbps 2-GFSK, 100-kHz channel	± 200 kHz (alternate channel)	43		
	separation, 20-kHz deviation, 100-kHz	± 1 MHz	62		
	channel filter	± 2 MHz	66		
		± 10 MHz	74		
		± 200 kHz (adjacent channel)	43		
	50-kbps 2-GFSK, 200-kHz channel separation, 25-kHz deviation, 100-kHz	± 400 kHz (alternate channel)	50		
	channel filter	± 1 MHz	61		
	(Same modulation format as 802.15.4g Mandatory Mode)	± 2 MHz	65		
	managery modely	± 10 MHz	74		
		± 200 kHz (adjacent channel)	36		
		± 400 kHz (alternate channel)	44		
	200-kbps 4-GFSK, 83-kHz deviation (outer symbols), 200-kHz channel filter, zero IF	± 1 MHz	55		
	5,500), 200 Kitz Giarrior mor, 2010 II	± 2 MHz	59		
		± 10 MHz	67		
mage rejec	tion (image compensation enabled)	1.2 kbps, DEV = 4 kHz CHF = 10 kHz <sup>(4)</sup> , image at -125 kHz	54		dB



## **Receive Parameters (continued)**

All RX measurements made at the antenna connector, to a bit error rate (BER) limit of 1%.

	PARAMETER	TEST CONDITIONS	MIN TYP M	AX UNIT
RX PERFOR	RMANCE IN 434-MHZ BAND (HIGH-PERI	FORMANCE MODE) (2)		
		1.2 kbps, DEV = 4 kHz CHF = 10 kHz <sup>(4)</sup>	-123	
Sensitivity		50 kbps 2GFSK, DEV = 25 kHz, CHF = 100 kHz	-109	dBm
		1.2 kbps, DEV = 20 kHz CHF = 50 kHz <sup>(4)</sup>	-116	
		± 12.5 kHz (adjacent channel)	60	
	1.2 kbps 2FSK, 12.5-kHz channel	± 25 kHz (alternate channel)	60	
	separation, 4-kHz deviation,	± 1 MHz	79	
	10-kHz channel filter	± 2 MHz	82	
		± 10 MHz	91	
		± 50 kHz (adjacent channel)	54	
Blocking	1.2 kbps 2FSK, 50-kHz channel	+ 100 kHz (alternate channel)	54	
and Selectivity	separation, 20-kHz deviation,	± 1 MHz	74	dB
	50-kHz channel filter	± 2 MHz	78	
		± 10 MHz	86	
	38.4 kbps 2GFSK, 100-kHz channel separation, 20-kHz deviation, 100-kHz channel filter	+ 100 kHz (adjacent channel)	47	
		± 200 kHz (alternate channel)	50	
		± 1 MHz	67	
		± 2 MHz	71	
		± 10 MHz	78	
RX PERFOR	RMANCE IN 169-MHZ BAND (HIGH-PERI	FORMANCE MODE) (2)		
Oistrate.		1.2 kbps, DEV = 4 kHz CHF = 10 kHz <sup>(4)</sup>	-123	-11
Sensitivity		1.2 kbps, DEV = 20 kHz CHF = 50 kHz <sup>(4)</sup>	-117	dbm
		± 12.5 kHz (adjacent channel)	64	
	1.2 kbps 2FSK, 12.5-kHz channel	± 25 kHz (alternate channel)	66	
	separation, 4-kHz deviation,	± 1 MHz	82	
	10-kHz channel filter	± 2 MHz	83	
Blocking		± 10 MHz	89	٦D
and Selectivity		± 50 kHz (adjacent channel)	60	dB
-	1.2 kbps 2FSK, 50-kHz channel	+ 100 kHz (alternate channel)	60	
	separation, 20-kHz deviation,	± 1 MHz	76	
	50-kHz channel filter	± 2 MHz	77	
		± 10 MHz	83	
Spurious response rejection	1.2 kbps 2FSK, 12.5-kHz channel separation, 4-kHz deviation, 10-kHz channel filter		70	dB
Image reject	ion (image compensation enabled)	1.2 kbps, DEV = 4 kHz CHF = 10 kHz <sup>(4)</sup> , image at -125 kHz	66	dB



### **Receive Parameters (continued)**

All RX measurements made at the antenna connector, to a bit error rate (BER) limit of 1%.

	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
RX PERFO	RMANCE IN LOW-POWER MODE <sup>(1)</sup>				
		1.2 kbps, DEV = 4 kHz CHF = 10 kHz <sup>(4)</sup>	-111		
Sensitivity		38.4 kbps, DEV = 50 kHz CHF = 100 kHz <sup>(4)</sup>	-99		dBm
		50 kbps 2GFSK, DEV = 25 kHz, CHF = 100 kHz <sup>(4)</sup>	-99		QDIII
		± 12.5 kHz (adjacent channel)	46		
	1.2 kbps 2FSK, 12.5-kHz channel	± 25 kHz (alternate channel)	46		
	separation, 4-kHz deviation,	± 1 MHz	73		
	10-kHz channel filter	± 2 MHz	78		
		± 10 MHz	79		
	1.2 kbps 2FSK, 50-kHz channel separation, 20-kHz deviation, 50-kHz channel filter	± 50 kHz (adjacent channel)	43		
		+ 100 kHz (alternate channel)	45		
		± 1 MHz	71		
		± 2 MHz	74		
Blocking		± 10 MHz	75		ID.
and Selectivity		+ 100 kHz (adjacent channel)	37		dB
•	38.4 kbps 2GFSK, 100-kHz channel	+ 200 kHz (alternate channel)	43		
	separation, 20-kHz deviation, 100-kHz	± 1 MHz	58		
	channel filter	± 2 MHz	62		
		+ 10 MHz	64		
		+ 200 kHz (adjacent channel)	43		
	50 kbps 2GFSK, 200-kHz channel separation, 25-kHz deviation, 100-kHz	+ 400 kHz (alternate channel)	52		
channel filter	channel filter	± 1 MHz	60		
	(Same modulation format as 802.15.4g	± 2 MHz	64		
	inalitatory initiatory	± 10 MHz	65		
Saturation			+10		dBm

### 4.6 Transmit Parameters

 $T_A$  = 25°C, VDD = 3.0 V,  $f_c$  = 869.5 MHz if nothing else stated

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
	At 950 MHz	+12		
	At 915- and 920-MHz	+14		
	At 915- and 920-MHz with VDD = 3.6 V	+15		
	At 868 MHz	+15		
Maximum output power	At 868 MHz with VDD = 3.6 V	+16		dBm
	At 433 MHz	+15		
	At 433 MHz with VDD = 3.6 V	+16		
	At 169 MHz	+15		
	At 169 MHz with VDD = 3.6 V	+16		
Minimum autout navor	Within fine step size range	-11		dBm
Minimum output power	Within coarse step size range	-40		UDIII
Output power step size	Within fine step size range	0.4		dB
	4-GFSK 9.6 kbps in 12.5-kHz channel, measured in 100-Hz bandwidth at 434 MHz (FCC Part 90 Mask D compliant)	<b>-75</b>		
Adjacent channel power	4-GFSK 9.6 kbps in 12.5-kHz channel, measured in 8.75-kHz bandwidth (ETSI EN 300 220 compliant)	-58		dBc
	2-GFSK 2.4 kbps in 12.5-kHz channel, 1.2-kHz deviation	-61		
Spurious emissions (not including harmonics)		<-60		dBm



## **Transmit Parameters (continued)**

 $T_A = 25^{\circ}C$ , VDD = 3.0 V,  $f_c = 869.5$  MHz if nothing else stated

	PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
	2nd Harm, 169 MHz			-39	
	3rd Harm, 169 MHz			<b>-</b> 58	
	2nd Harm, 433 MHz			<b>-</b> 56	
	3rd Harm, 433 MHz	Transmission at +14 dBm (or maximum allowed in		<del>-</del> 51	dBm
	2nd Harm, 450 MHz	applicable band where this is less than +14 dBm) using TI		-60	UDIII
	3rd Harm, 450 MHz	reference design Emissions measured according to ARIB T-96 in 950-MHz band, ETSI EN 300-220 in 170-, 433-,		<b>-45</b>	
Harmonics			-40		
			-42		
	2nd Harm, 915 MHz	transmitting for long intervals		56	
	3rd Harm, 915 MHz	(>50-ms periods)		52	dBµV/m
	4th Harm, 915 MHz			60	
	2nd Harm, 950 MHz			<b>-</b> 58	dBm
	3rd Harm, 950 MHz			-42	UDIII
Optimum	868-, 915-, and 920-MHz bands		35 -	+ j35	
load impedance 433 MHz band		55 -	+ j25	Ω	
Impodunoo	169 MHz band		80	+ j0	

### 4.7 PLL Parameters

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
HIGH-PERFORMANCE MODE		·		
	± 10 kHz offset	-99		
Phase noise in 950-MHz band	± 100 kHz offset	-99		dBc/Hz
	± 1 MHz offset	-123		
Phase noise in 868-, 915-, 920-MHz bands	± 10 kHz offset	-99		dBc/Hz
	± 100 kHz offset	-100		
	± 1 MHz offset	-122		
	± 10 kHz offset	-106		
Phase noise in 433-MHz band	± 100 kHz offset	-107		dBc/Hz
	± 1 MHz offset	-127		
	± 10 kHz offset	-111		
Phase noise in 169-MHz band	± 100 kHz offset	-116		dBc/Hz
	± 1 MHz offset	-135		



### PLL Parameters (continued)

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
LOW-POWER MODE <sup>(1)</sup>		<u> </u>	
	± 10 kHz offset	-90	
Phase noise in 950-MHz band	± 100 kHz offset	-92	dBc/Hz
	± 1 MHz offset	-124	
	± 10 kHz offset	<b>-95</b>	
Phase noise in 868-, 915-, 920-MHz bands	± 100 kHz offset	<b>-95</b>	dBc/Hz
	± 1 MHz offset	-124	
	± 10 kHz offset	-98	
Phase noise in 433-MHz band	± 100 kHz offset	-102	dBc/Hz
	± 1 MHz offset	-129	
	± 10 kHz offset	-106	
Phase noise in 169-MHz band	± 100 kHz offset	-110	dBc/Hz
	± 1 MHz offset	-136	

<sup>(1)</sup>  $T_A = 25$ °C, VDD = 3.0 V,  $f_c = 869.5$  MHz if nothing else stated

#### 4.8 32-MHz Clock Input (TCXO)

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
Clock frequency			31.25	32	33.6	MHz
	High input voltage	TCXO with CMOS output	1.4		VDD	
TCXO with CMOS output <sup>(1)</sup>	Low input voltage	directly coupled to pin EXT_OSC	0		0.6	V
Clipped sine output	Clock input amplitude (peak-to-peak)	TCXO clipped sine output connected to pin EXT_OSC through series capacitor	0.8		1.5	V

<sup>(1)</sup> For TCXO with CMOS output rise and fall time, see Section 4.15.

### 4.9 32-MHz Crystal Oscillator

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Crystal frequency	It is expected that there be will degraded sensitivity at multiples of XOSC/2 in RX, and an increase in spurious emissions when the RF channel is close to multiples of XOSC in TX. We recommend that the RF channel is kept RX_BW/2 away from XOSC/2 in RX, and that the level of spurious emissions be evaluated if the RF channel is closer than 1 MHz to multiples of XOSC in TX.	31.25	32	33.6	MHz
Load capacitance (C <sub>L</sub> )			10		pF
ESR	Simulated over operating conditions			60	Ω

### 4.10 32-kHz Clock Input

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

TA TO C, TTT CIC T II HOURING CICC CLARGE			
PARAMETER	MIN	TYP MAX	UNIT
Clock frequency		32	kHz
32-kHz clock input pin input high voltage	0.8 × VDD		V
32-kHz clock input pin input high voltage		0.2 × VDD	V



#### 4.11 32-kHz RC Oscillator

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Frequency	After calibration		32		kHz
Frequency accuracy after calibration	Relative to frequency reference (32-MHz crystal or TCXO)		±0.1%		
Initial calibration time <sup>(1)</sup>					

<sup>(1)</sup> For Initial calibration time of the 32-kHz RC Oscillator, see Section 4.15.

#### 4.12 I/O and Reset

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated

PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
Logic input high voltage		0.8 × VDD		V
Logic input low voltage			0.2 × VDD	V
Logic output high voltage	At A A start land land	0.8 × VDD		V
Logic output low voltage	At 4-mA output load or less		0.2 × VDD	V
Power-on reset threshold	Voltage on DVDD pin		1.3	V

### 4.13 Temperature Sensor

 $T_A = 25$ °C, VDD = 3.0 V if nothing else stated<sup>(1)</sup>

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Temperature sensor range		-40		85	°C
Temperature coefficient	Change in sensor output voltage versus change in temperature		2.66		mV/°C
Typical output voltage	Typical sensor output voltage at $T_A = 25$ °C, VDD = 3.0 V		794		mV
VDD coefficient	Change in sensor output voltage versus change in VDD		1.17		mV/V

<sup>(1)</sup> The CC1120 device can be configured to provide a voltage proportional to temperature on GPIO1. The temperature can be estimated by measuring this voltage (see Section 4.13, Temperature Sensor). For more information, refer to CC112X/CC120X On-Chip Temperature Sensor (SWRA415).

#### 4.14 Thermal Resistance Characteristics for RHB Package

NAME	DESCRIPTION	°C/W <sup>(1)</sup>
$R\Theta_{JC(top)}$	Junction-to-case (top)	21.1
$R\Theta_{JB}$	Junction-to-board	5.3
$R\Theta_{JA}$	Junction-to-free air	31.3
Psi <sub>JT</sub>	Junction-to-package top	0.2
Psi <sub>JB</sub>	Junction-to-board	5.3
RO <sub>JC(bot)</sub>	Junction-to-case (bottom)	0.8

<sup>(1)</sup> These values are based on a JEDEC-defined 2S2P system (with the exception of the Theta JC [RO<sub>JC</sub>] value, which is based on a JEDEC-defined 1S0P system) and will change based on environment as well as application. For more information, see these EIA/JEDEC standards:

- JESD51-2, Integrated Circuits Thermal Test Method Environmental Conditions Natural Convection (Still Air)
- JESD51-3, Low Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages
- JESD51-7, High Effective Thermal Conductivity Test Board for Leaded Surface Mount Packages
- JESD51-9, Test Boards for Area Array Surface Mount Package Thermal Measurements

Power dissipation of 40 mW and an ambient temperature of 25°C is assumed.



### 4.15 Timing Requirements

 $T_A = 25$ °C, VDD = 3.0 V,  $f_c = 869.5$  MHz if nothing else stated

PARA	METER	TEST CONDITIONS	MIN NOM MAX	UNIT	
Power down to IDLE		Depends on crystal	0.4	ms	
IDLE to DV/TV		Calibration disabled	166		
IDLE to RX/TX		Calibration enabled	461	μs	
RX/TX turnaround			50	μs	
DV/TV to IDI E time		Depends on crystal 0.4  Calibration disabled 166  Calibration enabled 461  50  Calibrate when leaving RX/TX enabled  Calibrate when leaving RX/TX disabled  When using SCAL strobe 391  12.5-kHz channels 4.6	296		
RX/TX to IDLE time			0	μs	
Frequency synthesizer calibration		When using SCAL strobe	391	μs	
Time from start RX until valid RSSI		12.5-kHz channels 4.6			
Including gain settling (function of che trade-off between speed and accura	nannel bandwidth. Programmable for cy)	200-kHz channels	0.3	ms	
32-MHz CLOCK INPUT (TCXO) <sup>(1)</sup>					
TCXO with CMOS output	Rise and fall time		2	ns	
32-kHz RC OSCILLATOR (2)				•	
Initial calibration time			1.6	ns	

<sup>(1)</sup> See Section 4.8 for more information about the 32-MHz Clock Input (TCXO).

### 4.16 Regulatory Standards

PERFORMANCE MODE	FREQUENCY BAND	SUITABLE FOR COMPLIANCE WITH
High-performance mode	820–960 MHz <sup>(1)</sup>	ARIB T-96 ARIB T-108 ETSI EN 300 220 category 2 ETSI EN 54-25 FCC PART 101 FCC PART 24 SUBMASK D FCC PART 15.247 FCC PART 15.249 FCC PART 90 MASK G FCC PART 90 MASK J
	410–480 MHz <sup>(2)</sup>	ARIB T-67 ARIB RCR STD-30 ETSI EN 300 220 category 1 FCC PART 90 MASK D FCC PART 90 MASK G
	164–192 MHz <sup>(2)</sup>	ETSI EN 300 220 category 1 FCC PART 90 MASK D
Low-power mode	820–960 MHz	ETSI EN 300 220 category 2 FCC PART 15.247 FCC PART 15.249
25 p.55	410–480 MHz	ETSI EN 300 220 category 2
	164–192 MHz	ETSI EN 300 220 category 2

<sup>(1)</sup> Performance also suitable for systems targeting maximum allowed output power in the respective bands, using a range extender such as the CC1190 device

<sup>(2)</sup> See Section 4.11 for more information about the 32-kHz RC Oscillator.

<sup>(2)</sup> Performance also suitable for systems targeting maximum allowed output power in the respective bands, using a range extender

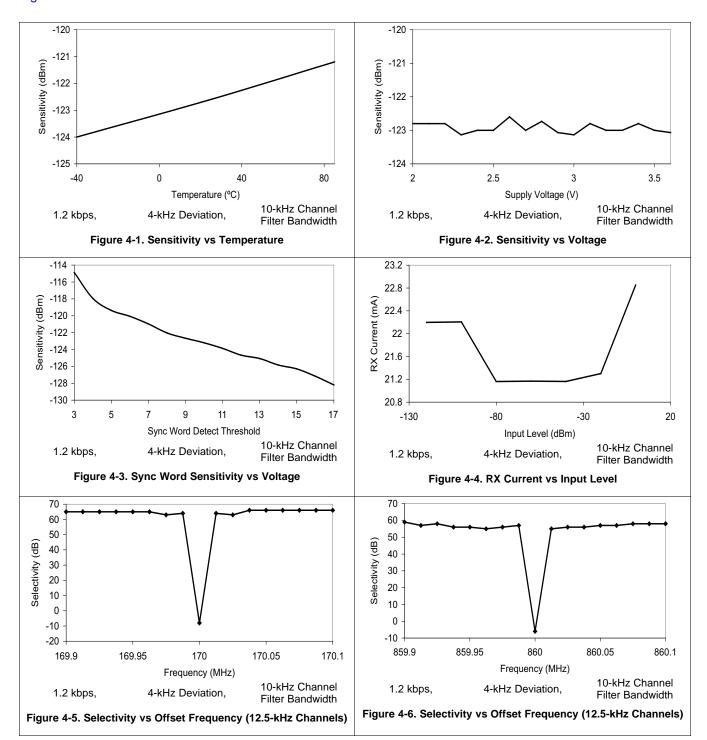


### 4.17 Typical Characteristics

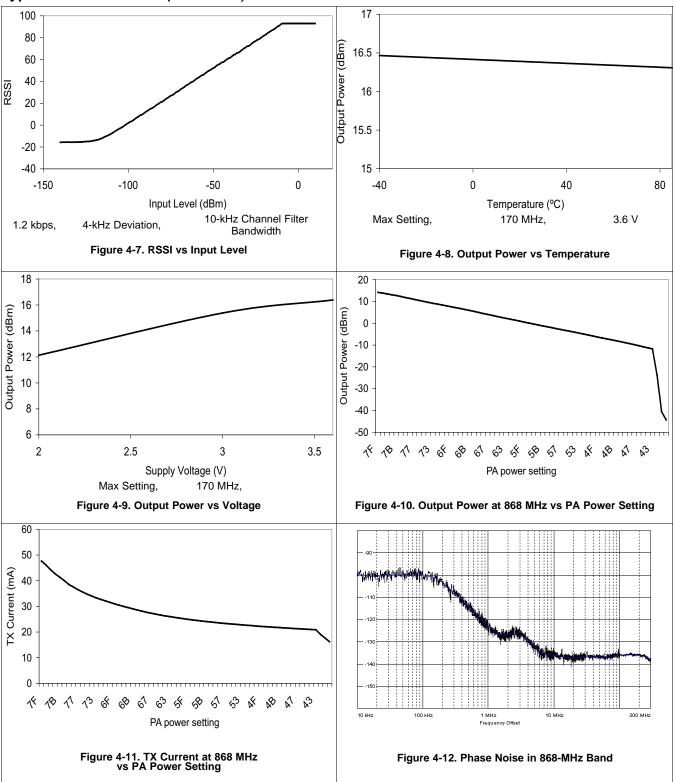
 $T_A = 25$ °C, VDD = 3.0 V,  $f_c = 869.5$  MHz if nothing else stated.

All measurements performed on CC1120EM\_868\_915 rev.1.0.1, CC1120EM\_955 rev.1.2.1, CC1120EM\_420\_470 rev.1.0.1, or CC1120EM\_169 rev.1.2.

Figure 4-17 was measured at the  $50-\Omega$  antenna connector.

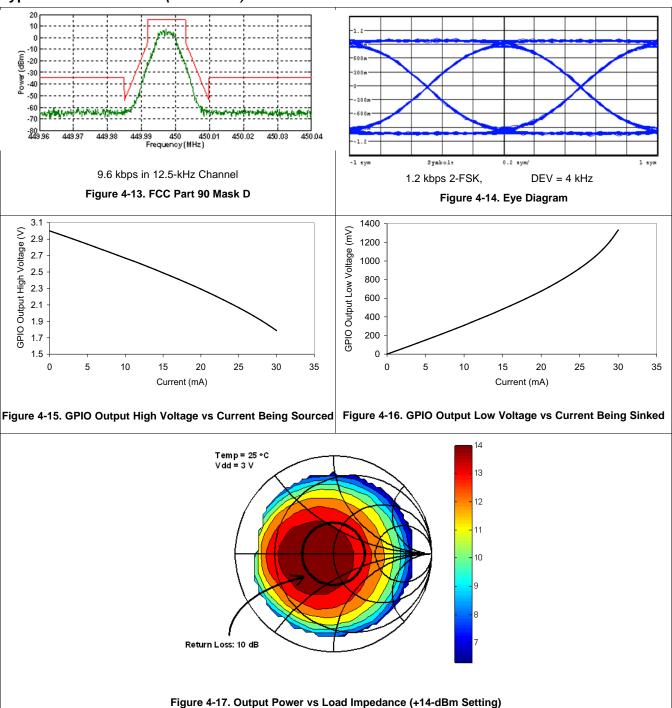


### Typical Characteristics (continued)





#### Typical Characteristics (continued)



### 5 Detailed Description

#### 5.1 Block Diagram

Figure 5-1 shows the system block diagram of the CC1120 devices.

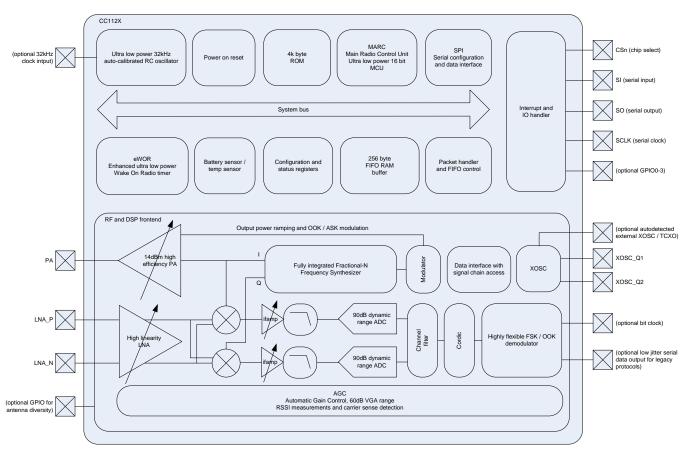


Figure 5-1. System Block Diagram

#### 5.2 Frequency Synthesizer

At the center of the CC1120 device there is a fully integrated, fractional-N, ultra-high-performance frequency synthesizer. The frequency synthesizer is designed for excellent phase noise performance, providing very high selectivity and blocking performance. The system is designed to comply with the most stringent regulatory spectral masks at maximum transmit power.

Either a crystal can be connected to XOSC\_Q1 and XOSC\_Q2, or a TCXO can be connected to the EXT\_XOSC input. The oscillator generates the reference frequency for the synthesizer, as well as clocks for the analog-to-digital converter (ADC) and the digital part. To reduce system cost, CC1120 device has high-accuracy frequency estimation and compensation registers to measure and compensate for crystal inaccuracies. This compensation enables the use of lower cost crystals. If a TCXO is used, the CC1120 device automatically turns on and off the TCXO when needed to support low-power modes and Wake-On-Radio operation.



#### 5.3 Receiver

The CC1120 device features a highly flexible receiver. The received RF signal is amplified by the low-noise amplifier (LNA) and is down-converted in quadrature (I/Q) to the intermediate frequency (IF). At IF, the I/Q signals are digitized by the high dynamic-range ADCs.

An advanced automatic gain control (AGC) unit adjusts the front-end gain, and enables the CC1120 device to receive strong and weak signals, even in the presence of strong interferers. High-attenuation channels and data filtering enable reception with strong neighbor channel interferers. The I/Q signal is converted to a phase and magnitude signal to support the FSK and OOK modulation schemes.

#### **NOTE**

A unique I/Q compensation algorithm removes any problem of I/Q mismatch, thus avoiding time-consuming and costly I/Q image calibration steps.

The CC1120 device only requires preamble to settle the AGC. The minimum number of preamble required is 0.5 byte.

#### 5.4 Transmitter

The CC1120 transmitter is based on direct synthesis of the RF frequency (in-loop modulation). To use the spectrum effectively, the CC1120 device has extensive data filtering and shaping in TX mode to support high throughput data communication in narrowband channels. The modulator also controls power ramping to remove issues such as spectral splattering when driving external high-power RF amplifiers.

#### 5.5 Radio Control and User Interface

The CC1120 digital control system is built around the main radio control (MARC), which is implemented using an internal high-performance, 16-bit ultra-low-power processor. MARC handles power modes, radio sequencing, and protocol timing.

A 4-wire SPI serial interface is used for configuration and data buffer access. The digital baseband includes support for channel configuration, packet handling, and data buffering. The host MCU can stay in power-down mode until a valid RF packet is received. This greatly reduces power consumption. When the host MCU receives a valid RF packet, it burst-reads the data. This reduces the required computing power.

The CC1120 radio control and user interface are based on the widely used CC1101 transceiver. This relationship enables an easy transition between the two platforms. The command strobes and the main radio states are the same for the two platforms.

For legacy formats, the CC1120 device also supports two serial modes.

- Synchronous serial mode: The CC1120 device performs bit synchronization and provides the MCU with a bit clock with associated data.
- Transparent mode: The CC1120 device outputs the digital baseband signal using a digital interpolation filter to eliminate jitter introduced by digital filtering and demodulation.

#### 5.6 Enhanced Wake-On-Radio (eWOR)

eWOR, using a flexible integrated sleep timer, enables automatic receiver polling with no intervention from the MCU. When the CC1120 device enters RX mode, it listens and then returns to sleep if a valid RF packet is not received. The sleep interval and duty cycle can be configured to make a trade-off between network latency and power consumption. Incoming messages are time-stamped to simplify timer resynchronization.

The eWOR timer runs off an ultra-low-power 32-kHz RC oscillator. To improve timing accuracy, the RC oscillator can be automatically calibrated to the RF crystal in configurable intervals.



#### 5.7 Sniff Mode

The CC1120 device supports quick start up times, and requires few preamble bits. Sniff mode uses these conditions to dramatically reduce the current consumption while the receiver is waiting for data.

Because the CC1120 device can wake up and settle much faster than the duration of most preambles, it is not required to be in RX mode continuously while waiting for a packet to arrive. Instead, the enhanced Wake-On-Radio feature can be used to put the device into sleep mode periodically. By setting an appropriate sleep time, the CC1120 device can wake up and receive the packet when it arrives with no performance loss. This sequence removes the need for accurate timing synchronization between transmitter and receiver, and lets the user trade off current consumption between the transmitter and receiver.

For more information, see the sniff mode design note (SWRA428).

#### 5.8 Antenna Diversity

Antenna diversity can increase performance in a multipath environment. An external antenna switch is required. The CC1201 device uses one of the GPIO pins to automatically control the switch. This device also supports differential output control signals typically used in RF switches.

If antenna diversity is enabled, the GPIO alternates between high and low states until a valid RF input signal is detected. An optional acknowledge packet can be transmitted without changing the state of the GPIO.

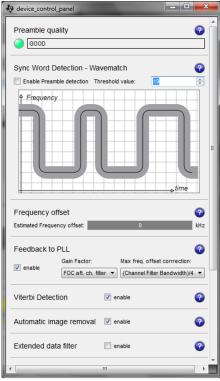
An incoming RF signal can be validated by received signal strength or by using the automatic preamble detector. Using the automatic preamble detector ensures a more robust system and avoids the need to set a defined signal strength threshold (such a threshold sets the sensitivity limit of the system).



#### 5.9 WaveMatch

Advanced capture logic locks onto the synchronization word and does not require preamble settling bytes. Therefore, receiver settling time is reduced to the settling time of the AGC, typically 4 bits.

The WaveMatch feature also greatly reduces false sync triggering on noise, further reducing the power consumption and improving sensitivity and reliability. The same logic can also be used as a high-performance preamble detector to reliably detect a valid preamble in the channel.



See SWRC046 for more information.

Figure 5-2. Receiver Configurator in SmartRF™ Studio

### 6 Application, Implementation, and Layout

#### **NOTE**

Information in the following Applications section is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### 6.1 Application Information

### 6.1.1 Typical Application Circuit

#### NOTE

This section is intended only as an introduction. The reference designs listed in Section 6.1.2 show everything required.

Very few external components are required for the operation of the CC1120 device. Figure 6-1 shows a typical application circuit. The board layout will greatly influence the RF performance of the CC1120 device. Figure 6-1 does not show decoupling capacitors for power pins.

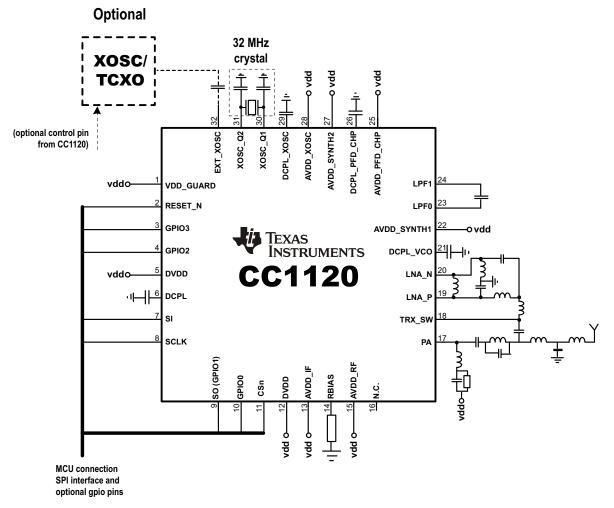


Figure 6-1. Typical Application Circuit

#### 6.1.2 TI Reference Designs

NSTRUMENTS

The following reference designs are available for the CC1120 device:

CC1120EM-868-915-RD CC1120EM 868- to 915-MHz Reference Design

This RF Layout Reference Design demonstrates good decoupling and layout techniques for a low power RF device operating in the 868-MHz and 915-MHz frequency bands.

CC1120EM 868/915 MHz Reference Design (SWRC222)

CC112x IPC 868- and 915-MHz 2-layer Reference Design (SWRR106)

CC112x IPC 868- and 915-MHz 4-layer Reference Design (SWRR107)

CC1120EM-169-RD CC1120EM 169-MHz Reference Design

This RF Layout Reference Design demonstrates good decoupling and layout techniques for a low power RF device operating in the 169-MHz frequency band. (SWRC220)

CC1120EM-420-470-RD CC1120EM 420- to 470-MHz Reference Design

This RF Layout Reference Design demonstrates good decoupling and layout techniques for a low power RF device operating in the 420-470 MHz frequency band. (SWRC221)

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### 7 Device and Documentation Support

#### 7.1 Device Support

#### 7.1.1 Development Support

#### 7.1.1.1 Configuration Software

The CC1120 device can be configured using the SmartRF Studio software (<u>SWRC046</u>). The SmartRF Studio software is highly recommended for obtaining optimum register settings, and for evaluating performance and functionality.

#### 7.1.2 Device and Development-Support Tool Nomenclature

To designate the stages in the product development cycle, TI assigns prefixes to the part numbers of all microprocessors (MPUs) and support tools. Each device has one of three prefixes: X, P, or null (no prefix) (for example, CC1120). Texas Instruments recommends two of three possible prefix designators for its support tools: TMDX and TMDS. These prefixes represent evolutionary stages of product development from engineering prototypes (TMDX) through fully qualified production devices and tools (TMDS).

Device development evolutionary flow:

X Experimental device that is not necessarily representative of the final device's electrical specifications and may not use production assembly flow.

P Prototype device that is not necessarily the final silicon die and may not necessarily meet final electrical specifications.

**null** Production version of the silicon die that is fully qualified.

Support tool development evolutionary flow:

**TMDX** Development-support product that has not yet completed Texas Instruments internal qualification testing.

**TMDS** Fully qualified development-support product.

X and P devices and TMDX development-support tools are shipped against the following disclaimer:

"Developmental product is intended for internal evaluation purposes."

Production devices and TMDS development-support tools have been characterized fully, and the quality and reliability of the device have been demonstrated fully. Tl's standard warranty applies.

Predictions show that prototype devices (X or P) have a greater failure rate than the standard production devices. Texas Instruments recommends that these devices not be used in any production system because their expected end-use failure rate still is undefined. Only qualified production devices are to be used.

TI device nomenclature also includes a suffix with the device family name. This suffix indicates the package type (for example, RHB) and the temperature range (for example, blank is the default commercial temperature range) provides a legend for reading the complete device name for any CC1120 device.

For orderable part numbers of CC1120 devices in the QFN package types, see the Package Option Addendum of this document, the TI website (www.ti.com), or contact your TI sales representative.



#### 7.2 Documentation Support

The following documents supplement the CC1120 transceiver. Copies of these documents are available on the Internet at <a href="www.ti.com">www.ti.com</a>. Tip: Enter the literature number in the search box provided at <a href="www.ti.com">www.ti.com</a>.

<u>SWRU295</u>	CC112X/CC1175 Low-Power High Performance Sub-1 GHz RF Transceivers/Transmitter User's Guide
<b>SWRA398</b>	Using the CC112x/CC1175 at 274 to 320 MHz
SWRC046	SmartRF Studio Software
<b>SWRA428</b>	CC112x/CC120x Sniff Mode Application Note
SWRZ039	CC112x, CC1175 Silicon Errata
<b>SWRR106</b>	CC112x IPC 868- and 915-MHz 2-layer Reference Design
<b>SWRR107</b>	CC112x IPC 868- and 915-MHz 4-layer Reference Design
SWRC220	CC1120EM 169-MHz Reference Design
SWRC221	CC1120EM 420- to 470-MHz Reference Design
SWRC222	CC1120EM 868- to 915-MHz Reference Design

#### 7.2.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

<u>Design Support</u> *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 7.3 Trademarks

SmartRF, E2E are trademarks of Texas Instruments.

#### 7.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 7.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

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### 8 Mechanical Packaging and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



### PACKAGE OPTION ADDENDUM

6-Feb-2020

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
CC1120RHBR	ACTIVE	VQFN	RHB	32	3000	Green (RoHS & no Sb/Br)	NIPDAU   NIPDAUAG	Level-3-260C-168 HR	-40 to 85	CC1120	Samples
CC1120RHBT	ACTIVE	VQFN	RHB	32	250	Green (RoHS & no Sb/Br)	NIPDAU   NIPDAUAG	Level-3-260C-168 HR	-40 to 85	CC1120	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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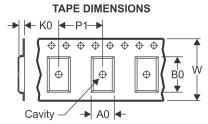
6-Feb-2020

### PACKAGE MATERIALS INFORMATION

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### TAPE AND REEL INFORMATION





A0	
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CC1120RHBR	VQFN	RHB	32	3000	330.0	12.4	5.3	5.3	1.5	8.0	12.0	Q2

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#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CC1120RHBR	VQFN	RHB	32	3000	350.0	350.0	43.0	

5 x 5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4224745/A





PLASTIC QUAD FLATPACK - NO LEAD



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
  2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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